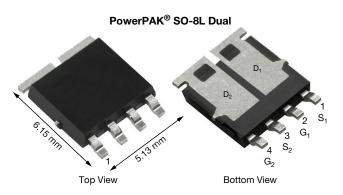


www.vishay.com

Vishay Siliconix

# Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.017			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.036			
I <sub>D</sub> (A)	- 30			
Configuration	Dual			

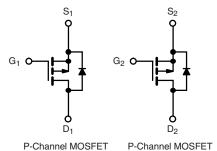
### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ951EP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	ss otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	- 30	
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current	$T_C = 25  ^{\circ}C^{a}$	1	- 30	
Continuous drain current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 28	
Continuous source current (diode conduction) a		I <sub>S</sub>	- 30	Α
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	- 120	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	- 27	
Single pulse avalanche energy	L=0.11III	E <sub>AS</sub>	36.5	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	56	W
Maximum power dissipation ~	T <sub>C</sub> = 125 °C	$P_{D}$	18.5	VV
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering recommendations (peak temperate	ure) <sup>e, f</sup>		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	85	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.7	G/VV

### Notes

- a. Package limited
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	•						,
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0, I <sub>D</sub> = - 250 μA	- 30	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V	-	-	- 1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> = - 5 V	- 30	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5 A	-	0.014	0.017	
Drain acuras an atata vasiatanas 8		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5A, T <sub>J</sub> = 125 °C	-	-	0.034	Ω
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5 A, T <sub>J</sub> = 175 °C	-	-	0.039	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 5 A	-	0.030	0.036	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	- 15 V, I <sub>D</sub> = - 7.5 A	-	18	-	S
Dynamic <sup>b</sup>	<u>.</u>						
Input capacitance	C <sub>iss</sub>			-	1345	1680	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 10 V, f = 1 MHz	-	330	415	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	245	305	
Total gate charge <sup>c</sup>	Qg			-	33	50	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -9 \text{ A}$	-	5.5	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	9.4		
Gate resistance	R <sub>g</sub>		f = 1 MHz	3	6.31	10.5	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	12	18	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> = -	- 15 V, R <sub>I</sub> = 1.66 Ω	-	12	18	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -9 A, Y$	$V_{\rm GEN} = -10  \text{V},  \text{R}_{\rm g} = 6  \Omega$	-	39	59	ns
Fall time <sup>c</sup>	t <sub>f</sub>	7		-	28	42	1
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	- 120	Α
Forward voltage	$V_{SD}$	I <sub>F</sub> = - 4.5 A, V <sub>GS</sub> = 0 0.		- 0.8	- 1.2	V	

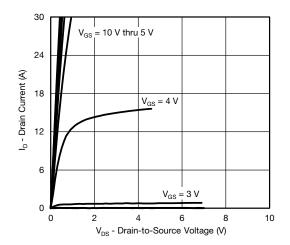
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

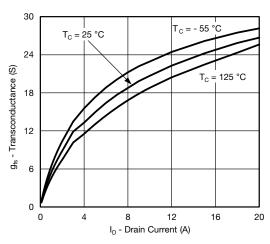
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



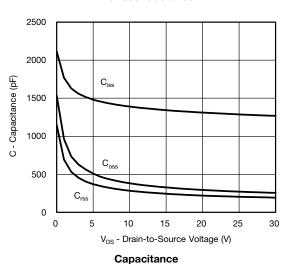
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### **Output Characteristics**

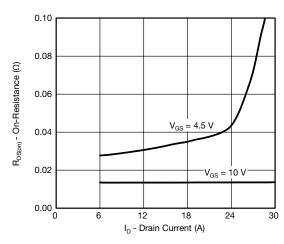


### Transconductance

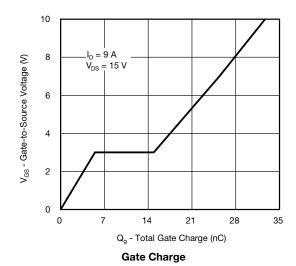


# 30 24 (x) 18 $T_{c} = 125 \, ^{\circ}\text{C}$ $T_{c} = 125 \, ^{\circ}\text{C}$ $T_{c} = -55 \, ^{\circ}\text{C}$

### **Transfer Characteristics**

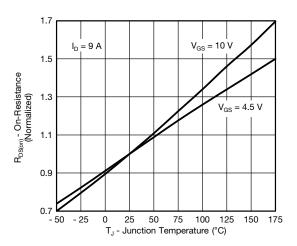


### **On-Resistance vs. Drain Current**

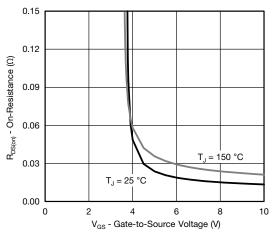


TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

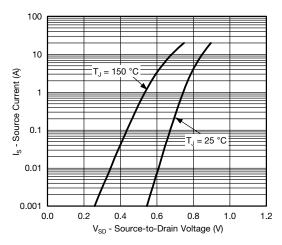




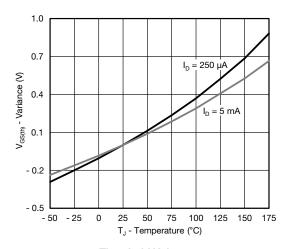
### On-Resistance vs. Junction Temperature



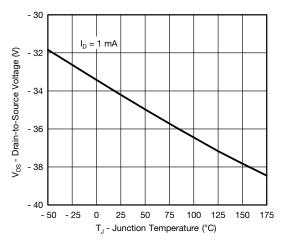
On-Resistance vs. Gate-to-Source Voltage



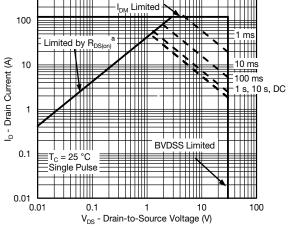
**Source Drain Diode Forward Voltage** 



### Threshold Voltage



**BVDSS** vs. Junction Temperature



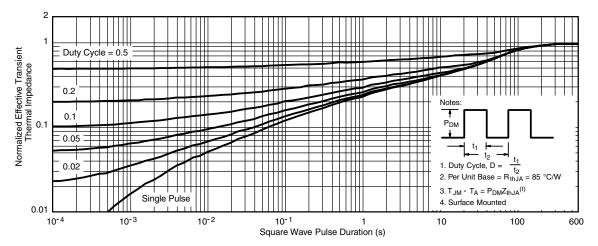
Safe Operating Area

### Note

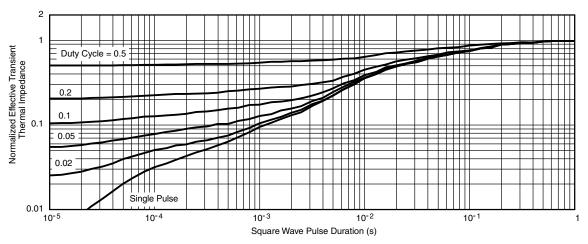
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

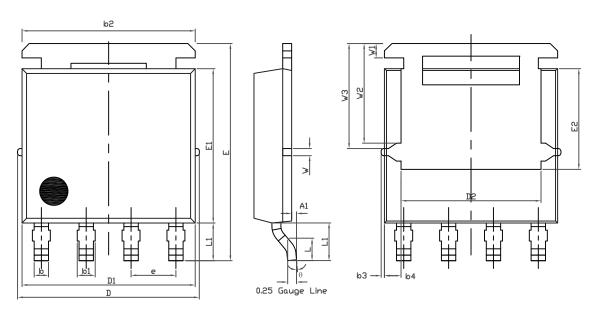


Normalized Thermal Transient Impedance, Junction-to-Case

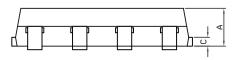
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?63658">www.vishay.com/ppg?63658</a>.

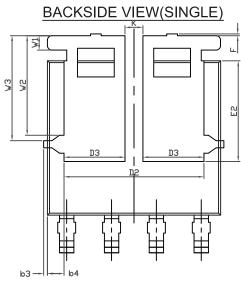


# PowerPAK® SO-8L Case Outline 2



**TOPSIDE VIEW** 





BACKSIDE VIEW(DUAL)



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM. MAX. MIN. NOM.				MAX	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23			0.009		
W1		0.41			0.016		
W2	2.82			0.111			
W3		2.96			0.117		
q	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. B, 05-Aug-2019

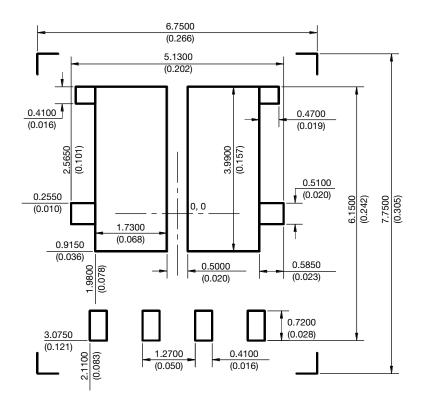
DWG: 6044

### Note

· Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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